MICROWAVE POWER GaAs FET TIM1314-15ULA

FEATURES

- •BROAD BAND INTERNALLY MATCHED FET •HIGH POWER
- P1dB= 42.0dBm at 13.75GHz to 14.5GHz

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

HIGH GAIN

G1dB= 7.0dB at 13.75GHz to 14.5GHz

- ·LOW INTERMODULATION DISTORTION
- IM3= -42dBc(Min.) at Pout= 30dBm (Single Carrier Level)

HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.	
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 4.0A f= 13.75 to 14.5GHz	dBm	41.0	42.0	_	
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.0	7.0	_	
Drain Current	IDS1		А		4.4	5.0	
Gain Flatness	ΔG		dB			±0.8	
Power Added Efficiency	ηadd		%		32		
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 30dBm, ∆f= 5MHz (Single Carrier Level)	dBc	-42	-45	_	
Drain Current	IDS2		А		4.0	5.0	
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C			80	

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 100 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 4.8A	S	_	4.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 145mA	V	-0.5	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	8.0	_
Gate-Source Breakdown Voltage	VGSO	IGS= -145μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		2.0	2.5

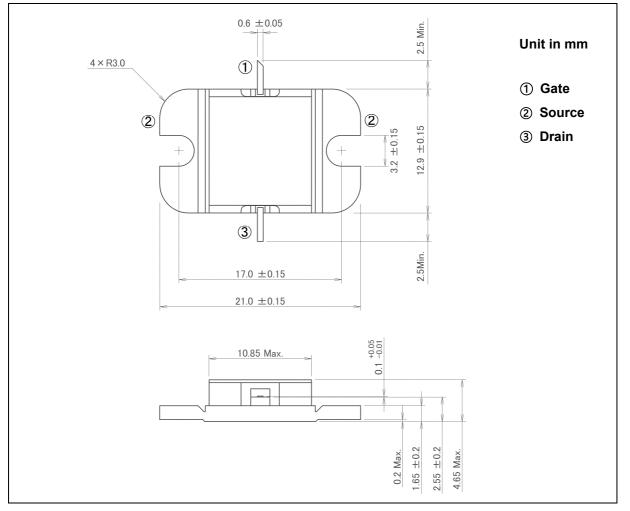
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	11.4
Total Power Dissipation (Tc= 25°C)	PT	W	60
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-11C1B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

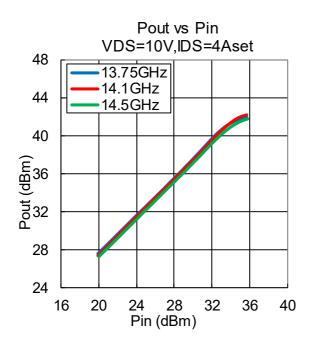
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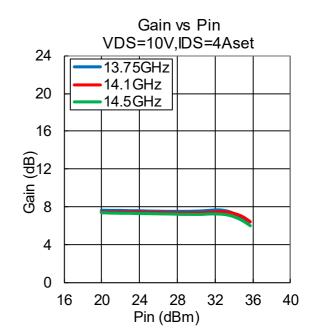
TYPICAL RF PERFORMANCE

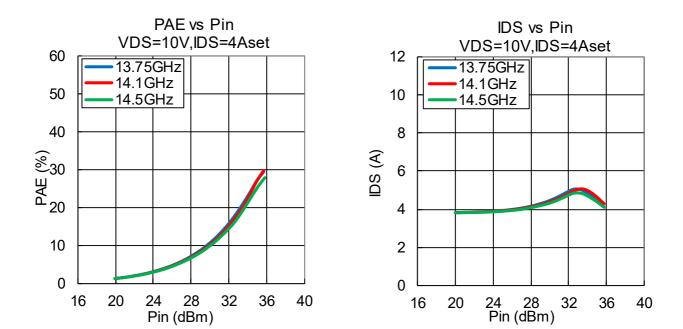
ROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 4.0 A, f= 13.75, 14.1, 14.5 GHz, Ta= +25 °C



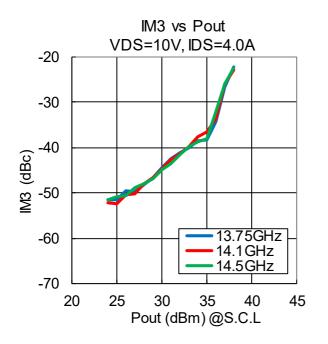


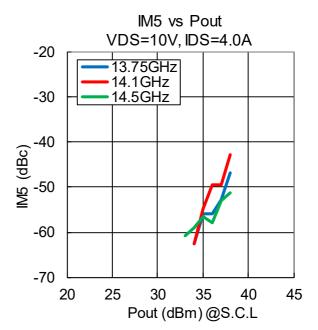


MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3, IM5 vs. Pout

VDS= 10 V, IDSset= 4.0 A, f= 13.75, 14.1, 14.5 GHz, Δ f= 5 MHz , Ta= +25 $^\circ$ C

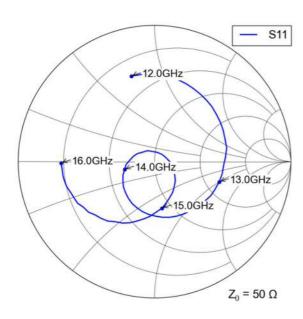


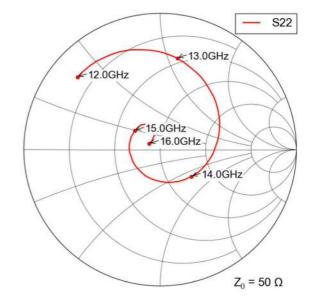


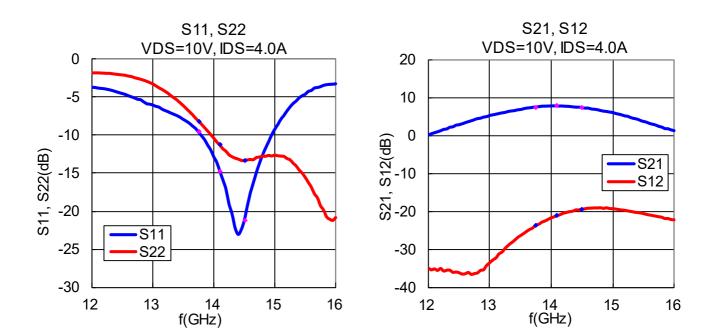
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 10 V, IDSset= 4.0 A, f= 12.0 to 16.0 GHz, Ta= +25 ℃







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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